

40V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

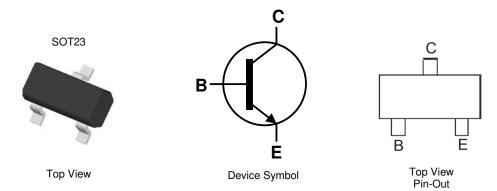
Features

- Complementary PNP Type Available (DIODES™ MMBT3906Q)
- Ideal for Medium Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ MMBT3904Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)



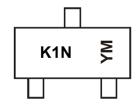
Ordering Information (Note 4)

Product	Package	Marking Reel Size	Reel Size (inches)	Tape Width (mm)	Pac	king
Floduct	Fackage	Warking	neer Size (Inches)	rape widin (ililii)	Qty.	Carrier
MMBT3904Q-7-F	SOT23	K1N	7	8	3,000	Reel
MMBT3904Q-13-F	SOT23	K1N	13	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K1N = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: J = 2022) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Date Code Rey												
Year	2014		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	В		J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	Ic	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	310	mW	
Power Dissipation	(Note 6)	P_{D}	350	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	Б	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	-C/VV	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 8)

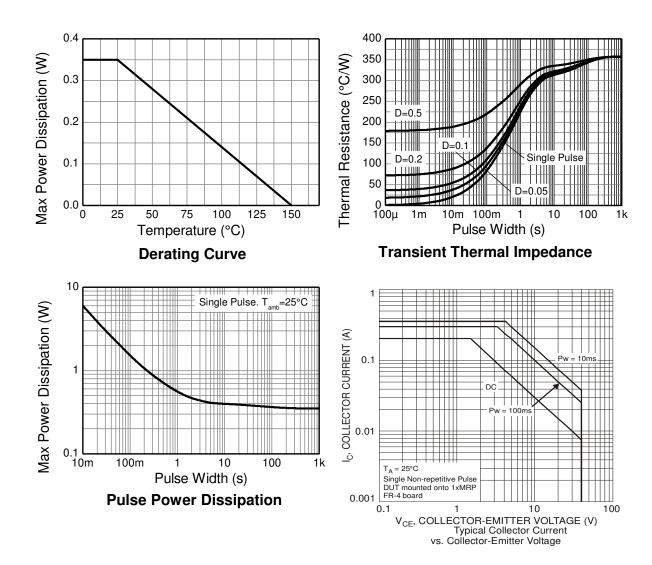
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 15 mm \times 15mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the leads).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS				•	
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	40	_	V	$I_C = 10mA, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	_	V	$I_E = 10\mu A, I_C = 0$
Collector Cut-Off Current	ICEX		50	nA	$V_{CE} = 30V$, $V_{EB(off)} = 3.0V$
Base Cut-Off Current	I_{BL}		50	nA	$V_{CE} = 30V$, $V_{EB(off)} = 3.0V$
Emitter Base Cut-Off Current	I _{EBO}		50	nA	$V_{EB} = 6V$
Collector-Base Cut-Off Current	I _{CBO}		50	nA	V _{CB} = 48V
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	_	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 1.0 V \\ I_C &= 1.0 m A, \ V_{CE} = 1.0 V \\ I_C &= 10 m A, \ V_{CE} = 1.0 V \\ I_C &= 50 m A, \ V_{CE} = 1.0 V \\ I_C &= 100 m A, \ V_{CE} = 1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.20 0.30	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.65	0.85 0.95	V	$I_C = 10mA, I_B = 1.0mA$ $I_C = 50mA, I_B = 5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Сово	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{IBO}	_	8.0	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$
Input Impedance	h _{IE}	1.0	10	kΩ	
Voltage Feedback Ratio	h _{RE}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{FE}	100	400	—	f = 1.0kHz
Output Admittance	hoE	1.0	40	μS	
Current Gain-Bandwidth Product	f _T	300	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz
Noise Figure	NF		5.0	dB	$V_{CE} = 5.0V$, $I_{C} = 100\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$
SWITCHING CHARACTERISTICS				•	•
Delay Time	t _d		35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	t _r		35	ns	$V_{BE(OFF)} = -0.5V$, $I_{B1} = 1.0mA$
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	t _f	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

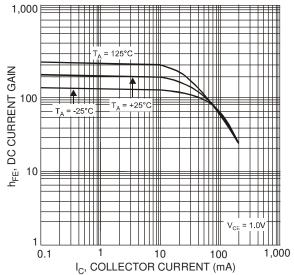
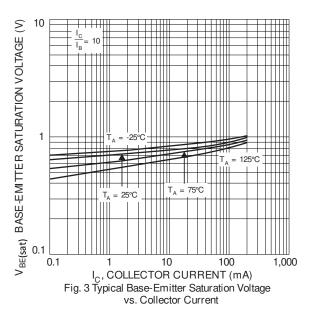


Fig. 1 Typical DC Current Gain vs. Collector Current



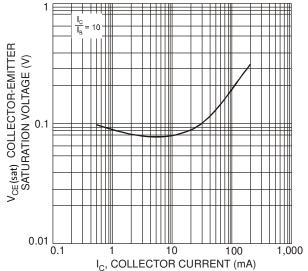


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

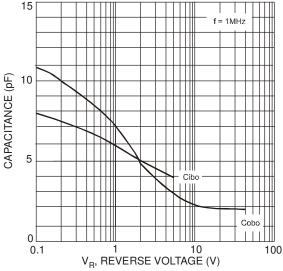


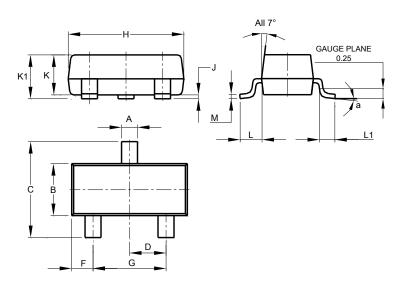
Fig. 4 Typical Capacitance Characteristics



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

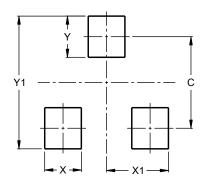


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
٦	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	29



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